

MT10N18S

N-Channel 100V Power MOSFET

Features

- 100V, 40A
- Typ $R_{DS(on)} = 17m\Omega$ (typ) @ $V_{GS} = 10V$
- Fast Switching Speed
- Low Gate Charge
- High Power and Current Handling Capability

General Description

This N-Channel MOSFET is produced using MOS-TECH Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Applications

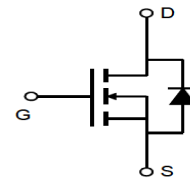
- DC-DC primary bridge
- DC-DC Synchronous rectification
- DC FAN



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Simplified Schematic



MARKING DIAGRAM & PIN ASSIGNMENT



Absolute Maximum Ratings (@ $T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ C$	A
		$T_C = 100^\circ C$	
I_{DM}	Pulsed Drain Current ⁽¹⁾	160	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	121	mJ
P_D	Power Dissipation	$T_C = 25^\circ C$	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2	$^\circ C/W$
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ C$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	I _D = 250μA, V _{GS} = 0V	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.7	2.5	V
R _{DS(ON)}	Static Drain-Source ON-Resistance ⁽³⁾	V _{GS} = 10V, I _D = 20A	-	17.0	28.0	mΩ
		V _{GS} = 4.5V, I _D = 10A	-	18.0	36.0	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz	-	5060	-	pF
C _{oss}	Output Capacitance		-	175	-	pF
C _{rss}	Reverse Transfer Capacitance		-	155	-	pF
Q _g	Total Gate Charge	V _{GS} = 0 to 10V V _{DS} = 50V, I _D = 20A	-	101	-	nC
Q _{gs}	Gate Source Charge		-	26	-	nC
Q _{gd}	Gate Drain("Miller") Charge		-	24	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On DelayTime	V _{GS} = 10V, V _{DD} = 50V I _D = 20A, R _{GEN} = 2.5Ω	-	20	-	ns
t _r	Turn-On Rise Time		-	24	-	ns
t _{d(off)}	Turn-Off DelayTime		-	45	-	ns
t _f	Turn-Off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	40	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	160	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 30A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F = 15A, di/dt = 100A/us	-	40	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	63	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $V_G = 10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$, $I_{AS} = 22\text{A}$
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit

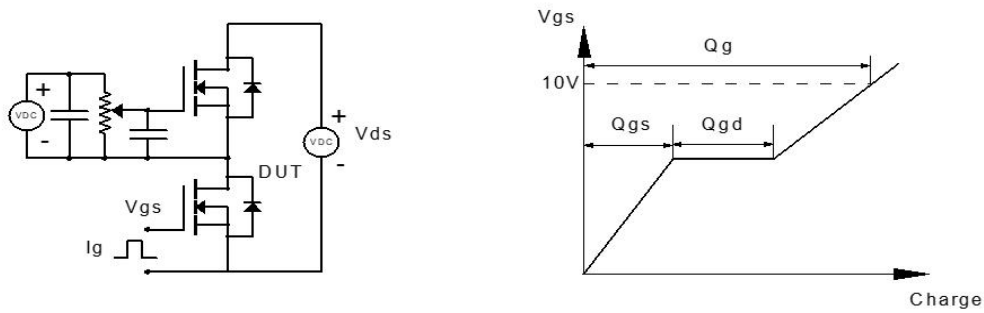


Figure 1: Gate Charge Test Circuit & Waveform

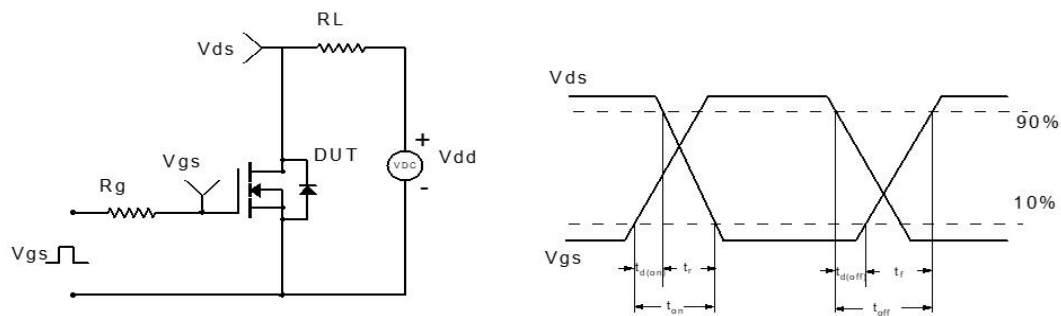


Figure 2: Resistive Switching Test Circuit & Waveform

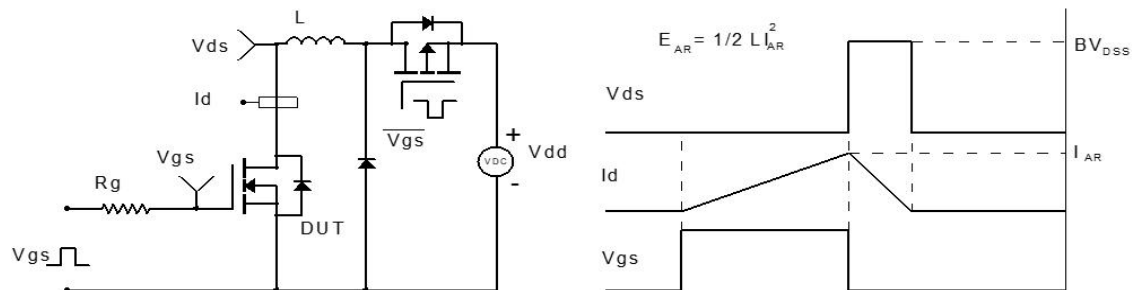


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

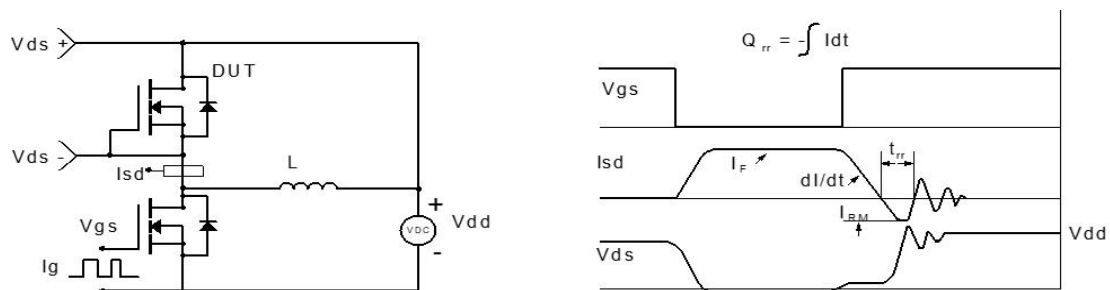
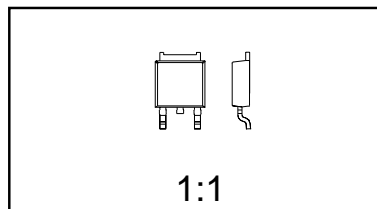
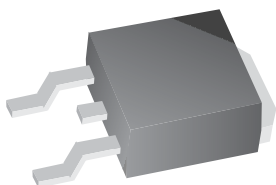


Figure 4: Diode Recovery Test Circuit & Waveform

Package Dimensions

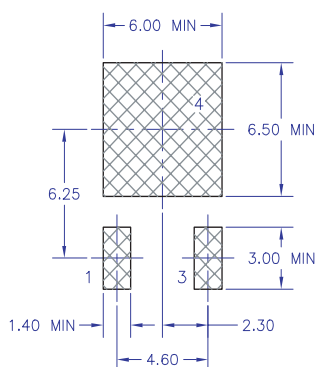
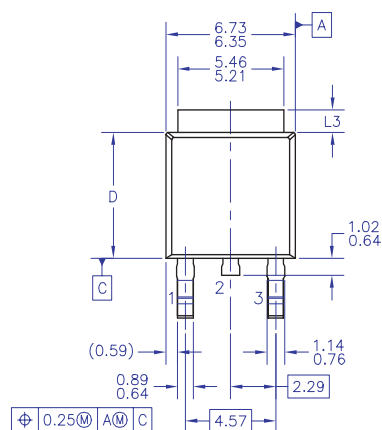
TO-252-2L



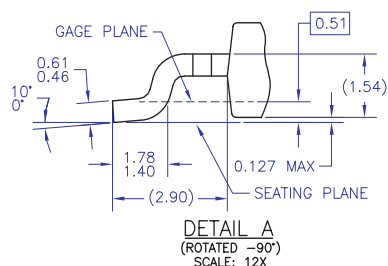
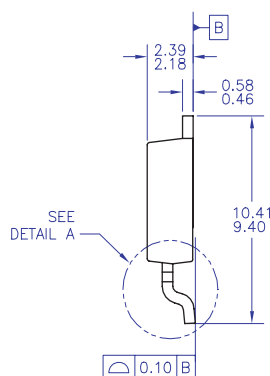
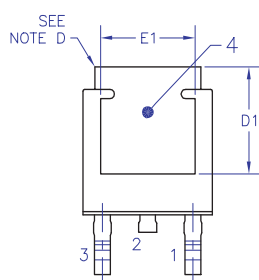
Scale 1:1 on letter size paper

Dimensions shown below are in:
millimeters

Part Weight per unit (gram): 0.33



LAND PATTERN RECOMMENDATION



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- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 B) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA & AB, DATED NOV. 1999.
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 D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
 E) DIMENSIONS L3,D,E1&D1 TABLE:

	OPTION AA	OPTION AB
L3	0.89-1.27	1.52-2.03
D	5.97-6.22	5.33-5.59
E1	4.32 MIN	3.81 MIN
D1	5.21 MIN	4.57 MIN

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